

ST1802HI

HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

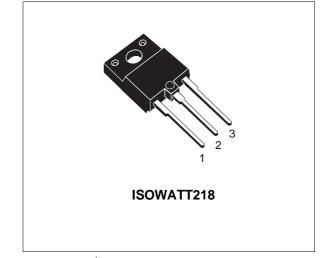
- NEW SERIES, ENHANCHED PERFORMANCE
- FULLY INSULATED PACKAGE FOR EASY MOUNTING
- HIGH VOLTAGE CAPABILITY
- HIGH SWITCHING SPEED
- TIGTHER hfe CONTROL
- IMPROVED RUGGEDNESS

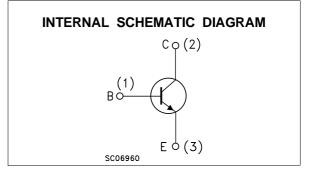
APPLICATIONS:

 HORIZONTAL DEFLECTION FOR COLOR TV

DESCRIPTION

The ST1802HI is manufactured using collector diffused technology for more stable operation Vs base drive circuit variations resulting in very low worst case dissipation.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{СВО}	Collector-Base Voltage (I _E = 0)	1500	V
Vceo	Collector-Emitter Voltage (I _B = 0)	600	V
V _{EBO}	Emitter-Base Voltage ($I_{C} = 0$)	7	V
Ι _C	Collector Current	8	А
Ісм	Collector Peak Current (t _p < 5 ms)	15	А
Ι _Β	Base Current	4	А
P _{tot}	Total Dissipation at $T_c = 25 \ ^{\circ}C$	50	W
T _{stg}	Storage Temperature	-65 to 150	°C
Tj	Max. Operating Junction Temperature	150	

THERMAL DATA

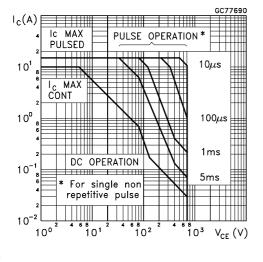
R _{thj-case} Thermal Resistance Junction-case	Max	2.5	°C/W
--	-----	-----	------

ELECTRICAL CHARACTERISTICS ($T_{case} = 25 \, {}^{\circ}C$ unless otherwise specified)

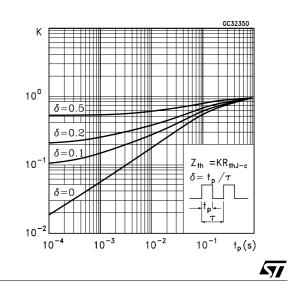
Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Unit
I _{CES}	Collector Cut-off Current (V _{BE} = 0)	V _{CE} = 1500 V V _{CE} = 1500 V	T _j = 125 ^o C			1 2	mA mA
I _{EBO}	Emitter Cut-off Current $(I_c = 0)$	V _{EB} = 7 V				1	mA
$V_{CEO(sus)}$	Collector-Emitter Sustaining Voltage	I _C = 100 mA	L = 25 mH	600			V
$V_{CE(sat)^*}$	Collector-Emitter Saturation Voltage	$I_{C} = 4 A$ $I_{C} = 4 A$	I _B = 0.8 A I _B = 1.2 A			5 1.5	V
V _{BE(sat)} *	Base-Emitter Saturation Voltage	I _C = 4.5 A	I _B = 1 A			1.2	V
h _{FE} *	DC Current Gain	$I_{C} = 1 A$ $I_{C} = 5 A$	V _{CE} = 5 V V _{CE} = 5 V	4	25	9	
t _s t _f	INDUCTIVE LOAD Storage Time Fall Time	I _C = 4 A L _B = 5 μH f = 16 KHz	$I_{BON(END)} = 1 A$ $V_{BB} = -2.5 V$		5 0.3	6 0.5	μs μs

 \ast Pulsed: Pulse duration = 300 $\mu s,$ duty cycle 1.5 %

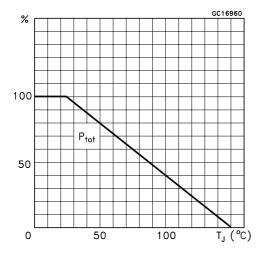
Safe Operating Areas



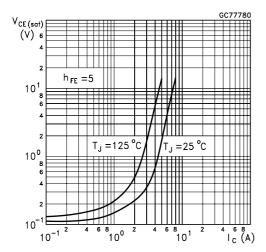
Thermal Impedance



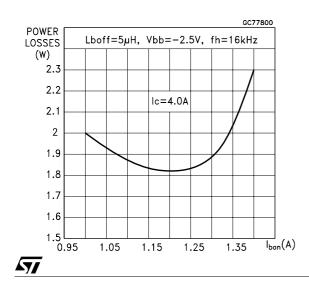
Derating Curve



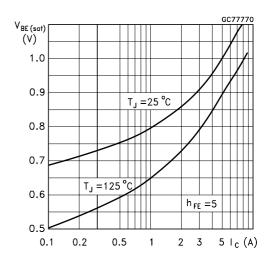
Collector Emitter Saturation Voltage



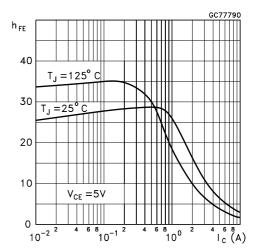
Power Losses At 16 KHz

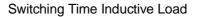


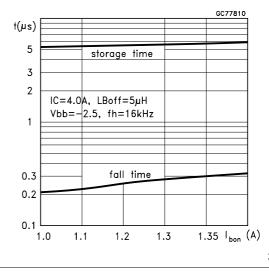
Base Emitter Saturation Voltage



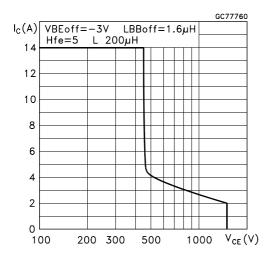
DC Current Gain



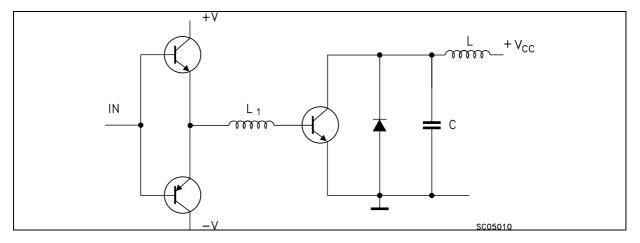




Reverse Biased SOA

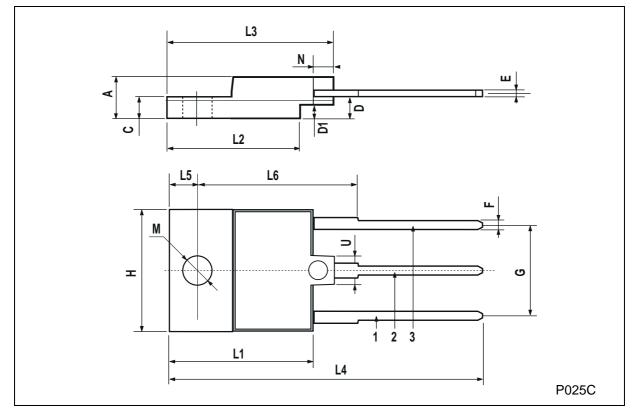


Inductive Load Switching Test Circuits.



DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	5.35		5.65	0.210		0.222
С	3.3		3.8	0.130		0.149
D	2.9		3.1	0.114		0.122
D1	1.88		2.08	0.074		0.081
Е	0.75		1	0.029		0.039
F	1.05		1.25	0.041		0.049
G	10.8		11.2	0.425		0.441
Н	15.8		16.2	0.622		0.637
L1	20.8		21.2	0.818		0.834
L2	19.1		19.9	0.752		0.783
L3	22.8		23.6	0.897		0.929
L4	40.5		42.5	1.594		1.673
L5	4.85		5.25	0.190		0.206
L6	20.25		20.75	0.797		0.817
М	3.5		3.7	0.137		0.145
Ν	2.1		2.3	0.082		0.090
U		4.6			0.181	





5/6

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specification mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics. The ST logo is a trademark of STMicroelectronics

© 1998 STMicroelectronics – Printed in Italy – All Rights Reserved STMicroelectronics GROUP OF COMPANIES Australia - Brazil - Canada - China - France - Germany - Italy - Japan - Korea - Malaysia - Malta - Morocco - The Netherlands -Singapore - Spain - Sweden - Switzerland - Taiwan - Thailand - United Kingdom - U.S.A.

57